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		Applicant(s): Hyungjun KIM et al.					
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U.S. PATENTS							
Initials	Patent Number	Issue Date	Name		Class	Sub-class	Filing date
	2003/0201537A U.S. Patent Application Serial No. 10/699,226	10/30/03	Lane et al. KIM et al.				
FOREIGN PATENT DOCUMENTS							
Initials	Document Number	Date	Country	Name		Translation? Yes/No/n/a	
OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)							
Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter-connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002							
KIM et. al., Growth of cubic-TaN thin films..J.App.Physics, Vol. 92, No.12,2002							
Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002							
Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J. Vac. Sci. Technol. B 20(4), J/A 2002							
Examiner's Signature:				Date Considered:			
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).							